



DSP Processors

## ABSTRACT

Hard and soft single-bit error will result in unexpected system behavior or even system crash. Error detection and correction in Keystone devices will improve system stability and reliability. This application report is focused on details on how ECC is implemented on Keystone devices for L1, L2, MSMC and DDR memory.

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## Table of Contents

<b>1 Introduction</b> .....	1
<b>2 Keystone Error Detection and Correction - EDC and Error Correcting Codes - ECC</b> .....	2
<b>3 References</b> .....	3
<b>4 Revision History</b> .....	3
<b>A Single Error Correct, Double Error Detection (SECEDED) Coverage on Keystone DSP Memories</b> .....	4

## List of Tables

Table 2-1. Arm-A15 Error Detection and Correction (ECC) Keystone Support.....	3
Table A-1. SECEDED Coverage on Keystone DSP Memories.....	4

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## 1 Introduction

Digital data is data that is represented using the binary number system of ones (1) and zeros (0). A single-bit error is when the electric charge of a bit changes, flipping it from a 0 to a 1, or vice versa. There are two main reasons for single-bit errors: hard or soft. Hard single-bit errors are caused by physical factors like temperature or power variation, and stress on the hardware. Soft single-bit errors result from factors that are harder to observe, such as magnetic interference and even cosmic rays. A flipped bit error could have a serious impact on important data: it may result in rather unexpected system behavior or even system crash. This is where ECC, Error-Correcting Code steps in. ECC is very popular in grid infrastructure, mission critical, aerospace and defense, or other critical systems with high-value data as it protects against data corruption by automatically detecting and correcting memory errors. System with ECC implementation is typically more stable and reliable than standard RAM.

## 2 Keystone Error Detection and Correction - EDC and Error Correcting Codes - ECC

Many applications have very stringent requirements to detect faults in the memory system of a processor to avoid failures of the end-system that could lead to dangerous situations for the end-user, or high requirements regarding the availability of the end-system. There are many mechanisms that could lead to faults in the memory of a processor. Some of these could lead to permanent faults and others to transient faults.

Detection of transient faults while the system is running is very important for critical applications. While permanent faults can be equally important, the likelihood of them occurring is usually significantly lower than transient faults. Permanent faults can, in many cases, be detected by running appropriate test algorithms at application startup or shutdown. Transient faults are faults predominantly introduced by soft errors. Major contributors of these are alpha radiation of the materials used in the package of a chip or neutron particles from cosmic rays. These can lead to bit flips in memories or changes to the state of a flip-flop.

There are multiple mechanisms in the Keystone architecture that is provided to detect such faults and in specific instances provide the ability to correct some of these faults.

### 2.1 Keystone Error Detection and Correct - EDC

#### 2.1.1 C66x L1P - EDC Implementation

L1P Error Detection Logic can detect single bit error for accesses that hit within L1P RAM or L1P cache. While the Error Detect logic is enabled, all 64-bit DMA writes will update and store parity and valid bits. Writes narrower than 64 bits (or) non-aligned writes will update the parity RAM to indicate 'invalid parity.' L1P checks parity for each program fetch on L1P as all the program fetches are 256-bit aligned. In the case of DMA/IDMA read access to L1P memory, the parity check occurs only when the data size is at least 64-bit wide or a multiple of 64-bit wide.

For full details on EDC Implementation in L1P on Keystone devices, see the [TMS320C66x DSP CorePac User's Guide](#).

#### 2.1.2 C66x L1D

No error detection or correction is implemented in L1D SRAM/Cache. The L1D is normally all cache, and the memory is usually temporary and in the rare instance of a bit flip that may occur it typically would not result in a system crash.

#### 2.1.3 C66x L2 - EDC Implementation

The L2 memory controller provides EDC with a hamming code capable of detecting double-bit errors and correcting single-bit errors within each 128-bit word. EDC is supported for both L2 RAM and L2 cache accesses. All 128-bit writes to L2 memory update the stored parity and valid bits in L2 RAM regardless of whether EDC logic is enabled or disabled. The L2 memory controller always performs a full hamming code check on 128-bit reads of L2 regardless of whether the fetch is from L1P, L1D, IDMA, or DMA. Writing narrower than 128 bits updates the parity RAM in L2 to indicate invalid parity and zeroes the parity values regardless of whether EDC is enabled or disabled. All 128-bit reads will be parity-checked when the EDC logic is enabled. L2 memory controller also applies EDC to L2 victims. Error Detection is performed on all L2 data fetches by L1D cache without any correction.

For full details on EDC Implementation in L1P on Keystone devices, see the [TMS320C66x DSP CorePac User's Guide](#).

### 2.2 Keystone MSMC RAM - EDC Implementation

The MSMC has error detection and correction hardware to protect the contents of the MSMC memory storage against corruption due to transient (soft) errors. The level of protection provided and the scheme used is the same as that of the C66x CorePacs (that is, one-bit error correction, two-bit error detection, with the parity codes calculated over a 256 bit datum).

The MSMC EDC hardware also provides a scrubbing engine which periodically cycles through each location of each memory bank in the MSMC, reading and correcting the data, recalculating the parity bits for the data, and storing the data and parity information. Each such "scrubbing cycle" consists of a series of read-modify-write "scrub bursts" to the memory banks.

For full details on EDC Implementation in MSMC, see the [KeyStone II Architecture Multicore Shared Memory Controller \(MSMC\) User's Guide](#) and the [KeyStone II Architecture Multicore Shared Memory Controller \(MSMC\) User's Guide](#).

## 2.3 Keystone DDR3 Error Correcting Code - ECC

For data integrity, the DDR3 memory controller supports ECC on the data written to or read from the ECC protected address ranges in memory. Eight-bit ECC is calculated over 64-bit data quanta and provides single error correction, double error detection (SECEDED) for the quanta. The system must ensure that any bursts accesses starting in the ECC protected region must not cross over into the unprotected region and vice-versa.

The ECC algorithm used in EMIF is the industry standard Hamming code (72,64) SECEDED algorithm.

For full details on EDC Implementation in MSMC, see the [KeyStone II Architecture Multicore Shared Memory Controller \(MSMC\) User's Guide](#) and the [KeyStone II Architecture Multicore Shared Memory Controller \(MSMC\) User's Guide](#).

## 2.4 Arm®-A15 Error Detection and Correction (ECC) Keystone Support

**Table 2-1. Arm-A15 Error Detection and Correction (ECC) Keystone Support**

Memory	Protection	Notes
L1 Data RAM	ECC (per 32 bits)	1-bit evict corrected line to L2, treat as L1D miss and refetch from L2; 2-bit detect
L2 Data RAM	ECC (per 64 bits)	1-bit inline correct to reader and evict (corrected); 2-bit detect
L1 Instruction Data RAM	Parity (per 16 bits)	1-bit detect, invalidate, and treat as cache miss (fetch from L2/DDR)
L1 Instruction Tag RAM	Parity	1-bit detect and treat as cache miss (fetch from L2/DDR)
L1 instruction BTB RAM	Parity	1-bit detect and treat as branch predictor miss
L1 Instruction GHB RAM	None	Error looks like prefetched the wrong address, effectively a predictor miss
L1 Instruction Indirect Predictor RAM	None	Error looks like prefetched the wrong address, effectively a predictor miss
L1 Data Tag RAM	ECC	1-bit evict corrected line to L2, treat as L1D miss and refetch from L2; 2-bit detect
L2 TLB RAM	Parity	TLB entry invalidate, trigger page walk
L2 tag RAM	ECC	1-bit correct (read-correct-write), replay lookup; 2-bit detect
L2 Snoop Tag RAM	ECC	1-bit correct (read-correct-write), replay lookup; 2-bit detect
L2 dirty RAM	ECC	1-bit evict cache line to DDR, replay load; 2-bit detect
L2 Prefetch RAM	Parity	1-bit invalidate line

For full details on the Arm A15 Implementation, see device-specific Arm Technical Reference Manual.

## 3 References

- Texas Instruments: [TMS320C66x DSP CorePac User's Guide](#)
- Texas Instruments: [KeyStone Architecture Multicore Shared Memory Controller \(MSMC\) User's Guide](#)
- Texas Instruments: [KeyStone II Architecture Multicore Shared Memory Controller \(MSMC\) User's Guide](#)
- Texas Instruments: [Keystone Architecture DDR3 Memory Controller User's Guide](#)
- Texas Instruments: [Keystone II Architecture DDR3 Memory Controller User's Guide](#)
- Texas Instruments: [Radiation Handbook for Electronics](#)

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision * (February 2020) to Revision A (June 2021)	Page
• Updated the numbering format for tables, figures and cross-references throughout the document.....	1

## A Single Error Correct, Double Error Detection (SECEDED) Coverage on Keystone DSP Memories

### A.1 SECEDED Coverage on Keystone DSP Memories

**Table A-1. SECEDED Coverage on Keystone DSP Memories**

Device Memories	C665x	C667x	66AK2K	66AK2H	66AK2L	66AK2E	66AK2G
ARM L1P	NA	NA	Parity	Parity	Parity	Parity	Parity
ARM L1D	NA	NA	ECC	ECC	ECC	ECC	ECC
ARM L2 Cache	NA	NA	ECC	ECC	ECC	ECC	ECC
On-Chip SRAM (OCMC/MSMC)	ECC						
PRU ICSS RAM(s)	NA	NA	NA	NA	NA	NA	ECC
DSP L1P Cache	Parity						
DSP L1D Cache	No	No	No	No	No	No	ECC
DSP L2 Cache	ECC						
General-Purpose Memory Controller (GPMC) - NAND	ECC						
External DRAM Controller 1 (EMIF1)	ECC						
External DRAM Controller 2 (EMIF2)	NA	NA	ECC	ECC	NA	NA	NA

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Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
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